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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/825,372	04/16/2004	Howard E. Rhodes	M4065.0105/P105-C	8394

24998 7590 12/13/2005

DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP  
2101 L Street, NW  
Washington, DC 20037

EXAMINER
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NGUYEN, TUAN H

ART UNIT	PAPER NUMBER
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2813

DATE MAILED: 12/13/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

EX

<b>Office Action Summary</b>	<b>Application No.</b>		<b>Applicant(s)</b>	
	10/825,372		RHODES, HOWARD E.	
	<b>Examiner</b>		<b>Art Unit</b>	
	Tuan H. Nguyen		2813	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

**Period for Reply**

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

**Status**

- 1) ☒ Responsive to communication(s) filed on 10 November 2005.
- 2a) ☐ This action is **FINAL**.                      2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

**Disposition of Claims**

- 4) ☒ Claim(s) 124-137, 170-188 and 200-209 is/are pending in the application.
- 4a) Of the above claim(s) 124-137 and 170-188 is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 200-209 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

**Application Papers**

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.  
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

**Priority under 35 U.S.C. § 119**

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All    b) ☐ Some \*    c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
  2. ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.
  3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

\* See the attached detailed Office action for a list of the certified copies not received.

**Attachment(s)**

- |   |   |
|---|---|
| 1) <input type="checkbox"/> Notice of References Cited (PTO-892)                        | 4) <input type="checkbox"/> Interview Summary (PTO-413)                     |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948)    | Paper No(s)/Mail Date. _____  |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) | 5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| Paper No(s)/Mail Date _____   | 6) <input type="checkbox"/> Other: _____                                    |

## DETAILED ACTION

### *Claim Rejections - 35 USC § 102*

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 200-204, 206, 209 are rejected under 35 U.S.C. 102(b) as being anticipated by Yamada et al. (cited ref.).

Yamada, figs. 4-5 and related text on col. 4-6 discloses the claimed method for forming a photosensor comprising excavating a trench within the semiconductor substrate, the trench having a substantially vertical internal surface and bottom surface region (fig. 5(e)-5(f), col. 5, next to last paragraph); performing a first and second implantation into the vertical internal surface region and the bottom surface region of the trench at first and second implantation angles (fig. 5(g)-5(j) and related text in col. 5-6, paragraphs (4)- (5)); forming a conductive layer 313 that covers the vertical internal surface region and bottom surface region of the trench (figs 5 (k)-(l) and col. 6, paragraph (6)).

With respect to claim 201, col. 6, paragraph (5) teaches the second implantation to the inside of the trench in a rotating manner that includes orthogonal angle to the first implantation.

With respect to claim 202, figs. 5(g)-5(j) show a plurality of ion implantations at a respective plurality of ion implantation angles.

With respect to claims 203, 204, col. 6, lines 12-14 discloses the formation of silicon dioxide above the vertical internal surface region.

With respect to claim 206, col. 5, line 62 discloses the use of PSG film 309 above the vertical internal surface region.

***Claim Rejections - 35 USC § 103***

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 205, 207, 208 are rejected under 35 U.S.C. 103(a) as being unpatentable over Yamada et al. in view of the admitted prior art.

Yamada, figs. 4-5 and related text on col. 4-6 discloses the claimed method for forming a photosensor except the use of BPSG or BSG as a passivation layer and CMP for a subsequent step of forming contact and wiring.

However, in paragraphs bridging pages 16-17, applicant clearly admitted that BPSG, PSG, or BSG are well-known material for use in passivating the device and CMP is a well-known process for planarizing in the final steps of forming contact and wiring.

Accordingly, it would have been obvious to one having ordinary skill in the art at the time the invention was made to have used the well-known BSP or BPSG material

and CMP process in forming contact and wiring as admitted as prior art in Yamada et al. process for completing the device as in the instant claimed invention.

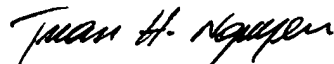
### ***Response to Arguments***

Applicant's arguments filed 10/26/05 have been fully considered but they are not persuasive. Since Yamada clearly teaches the ion implantations at different angles for forming a doped region along the vertical and bottom surfaces of the trench as the same as in the instant invention, and in order to form doped region at opposite walls of the trench, the ions are implanted in the opposite directions, each perpendicular to the charge transfer direction which is along the trench surface, in other words, the implantation angles are orthogonal to each other.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Tuan H. Nguyen whose telephone number is 571-272-1694. The examiner can normally be reached on 9AM-5:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead Jr. can be reached on 571-272-1702. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

  
Tuan H. Nguyen  
Primary Examiner  
Art Unit 2813